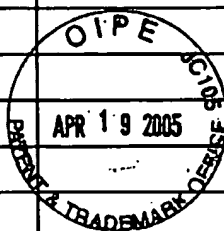


SUBSTITUTE FORM PTO-1449 (MODIFIED) INFORMATION DISCLOSURE STATEMENT BY APPLICANT (37 CFR 1.98(b))	U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE	ATTY. DOCKET NO. BEET/09	SERIAL NO. 10/524,525
	APPLICANT Martin Hausner		
	FILING DATE February 11, 2005	CONFIRMATION NO. 1134	

U.S. PATENT DOCUMENTS

EXAMINER INITIAL		PATENT NUMBER	ISSUE DATE	PATENTEE	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
	A.A						
	A.B						
	A.C						
	A.D						
	A.E						
	A.F						
	A.G						
	A.H						
	A.I						
	A.J						
	A.K						



FOREIGN PATENTS OR PUBLISHED FOREIGN PATENT APPLICATIONS

		DOCUMENT NUMBER	PUBLICATION DATE	COUNTRY OR PATENT OFFICE	CLASS	SUBCLASS	TRANSLATION (YES/NO)
/SA/	A.L	KR 2002041363A	06/2002	Republic of Korea	H01L	21/3065	No
	A.M						
	A.N						
	A.O						
	A.P						
	A.Q						

OTHER DOCUMENTS (Including Author, Title, Date, Place of Publication)

/SA/	A.R	Ayon et al., <u>Characterization of a Time Multiplexed Inductively Coupled Plasma Etcher</u> , Journal of the Electrochemical Society, January 1999, Vol. 146, Issue 1, pp. 339-349					
/SA/	A.S	The International Bureau of WIPO, <u>English Translation of the International Preliminary Examination Report</u> , November 17, 2004 (12 pages)					
	A.T						
EXAMINER /Shamim Ahmed/ (04/11/2007)				DATE CONSIDERED 04/11/2007			

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(MODIFIED)U.S. DEPARTMENT OF COMMERCE
PATENT AND TRADEMARK OFFICEATTY.CKET NO.
BEET/09EXPRESS MAIL NO.
EV 256143525INFORMATION DISCLOSURE
STATEMENT BY APPLICANT

(Use several sheets if necessary)

(37 CFR 1.98(b))

APPLICANT
Martin HausnerFILING DATE
February 11, 2005GROUP
Unknown

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/SA/	A.A	6	0	7	4	9	4	6	06/2000	Ouellet et al.	438	689	02/1997
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	A.C												
	A.D												
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	A.G												
	A.H												
	A.I												
	A.J												
	A.K												

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		DOCUMENT NUMBER	PUBLICATION DATE	COUNTRY OR PATENT OFFICE	CLASS	SUBCLASS	TRANSLATION (YES/NO)
/SA/	A.L	DE 196 41 288 A1	04/1998	Germany	C23F	4/00	No
	A.M	DE 197 36 370 C2	12/2001	Germany	H01L	21/3065	No
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/SA/	A.R	Ayon et al., <u>Anisotropic silicon trenches 300-500 um deep employing time multiplexed deep etching (TMDE)</u> , Sensors and Actuators A, Vol. 91, 2001, pp. 381-385					
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/SA/	A.T	Dijkstra et al., <u>Can SEA (Semiconductor Equipment Assessment) also deliver for MEMS?</u> , Horological Journal, Ashford, GB, Vol. 556, No. 302, 2001, pp. 684-690					

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